


FEATURES

- Direct Replacement for HCPL4503
- High Speed Optocoupler without Base Connection
- GaAlAs Emitter
- Integrated Detector with Photodiode and Transistor
- High Data Transmission Rate: 1 Mbit/s
- TTL Compatible
- Open Collector Output
- CTR at $I_F=16$ mA, $V_O=0.4$ V, $V_{CC}=4.5$ V, $T_A=25^\circ\text{C}$: $\geq 19\%$
- Good CTR Linearity Relative to Forward Current
- Field Effect Stable
- Low Coupling Capacitance
- Very High Common Mode Transient Immunity $dV/dt: \geq 15$ kV/ μs at $V_{CM}=1500$ V
- Insulation Test Voltage: 5300 VAC_{PK}
-  VDE 0884 Available with Option 1
- UL Approval, File #E52744

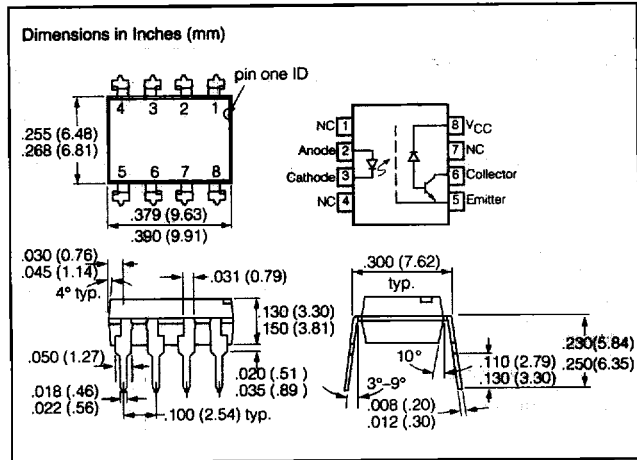
APPLICATIONS

- Data Communications
- IGBT Drivers
- Programmable Controllers

DESCRIPTION

The SFH6345 is an optocoupler with a GaAlAs infrared emitting diode, optically coupled to an integrated photodetector consisting of a photodiode and a high speed transistor in a DIP-8 plastic package. The device is similar to the 6N135 but has an additional Faraday shield on the detector which enhances the input-output dV/dt immunity.

Signals can be transmitted between two electrically separated circuits up to frequencies of 2 MHz. The potential difference between the circuits to be coupled should not exceed the maximum permissible reference voltages.



Absolute Maximum Ratings

Emitter (GaAlAs)

Reverse Voltage	3 V
DC Forward Current	25 mA
Surge Forward Current ($t_p \leq 1 \mu\text{s}$, 300 pulses/sec.)	1 A
Total Power Dissipation	45 mW

Detector (Si Photodiode + Transistor)

Supply Voltage	-0.5 to 30 V
Output Voltage	-0.5V to 25 V
Output Current	8 mA
Total Power Dissipation	100 mW

Package Insulation

Isolation Test Voltage	5300 VAC _{PK}
between emitter and detector	5300 VAC _{PK}
(refer to climate DIN 40046, part 2, Nov. 74)	

Creepage ≥ 7 mm min.

Clearance ≥ 7 mm min.

Comparative Tracking Index

per DIN IEC 112/VDE0303, part 1 ≥ 175

Isolation Resistance

$V_{IO}=500$ V, $T_A=25^\circ\text{C}$, R_{ISOL} $\geq 10^{12} \Omega$

$V_{IO}=500$ V, $T_A=100^\circ\text{C}$, R_{ISOL} $\geq 10^{11} \Omega$

Storage Temperature Range -55 to $+150^\circ\text{C}$

Ambient Temperature Range -55 to $+100^\circ\text{C}$

Junction Temperature 100°C

Soldering Temperature ($t=10$ sec. max.) 260°C

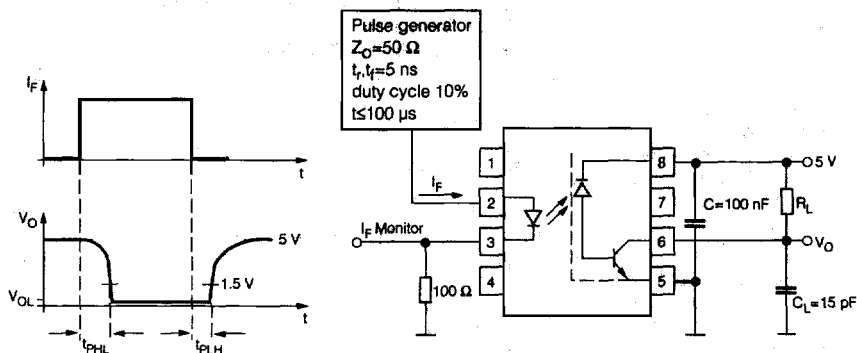
Dip soldering: distance to seating plane ≥ 1.5 mm

Optocouplers
(Semiconductors)

Characteristics ($T_A=0^\circ$ to 70°C , unless otherwise specified, typical values $T_A=25^\circ\text{C}$)

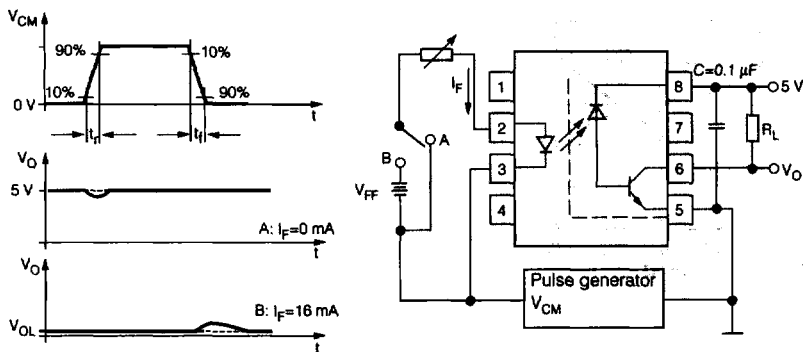
Description	Symbol	Min.	Typ.	Max.	Unit	Condition
Emitter (IR GaAlAs)						
Forward Voltage	V_F		1.6	1.9	V	$I_F=16\text{ mA}$
Reverse Current	I_R		0.5	10	μA	$V_R=3\text{ V}$
Capacitance	C_0		75		pF	$V_R=0\text{ V}$, $f=1\text{ MHz}$
Thermal Resistance	$R_{\theta JA}$		700		$^\circ\text{K/W}$	
Detector (Si Photodiode + Transistor)						
Supply Current, Logic High	I_{CCH}		0.01	1	μA	$I_F=0$, V_O (open), $V_{CC}=15\text{ V}$, $T_A=25^\circ\text{C}$
				2		$I_F=0$, V_O (open), $V_{CC}=15\text{ V}$
Output Current, Output High	I_{OH}		.003	0.5	μA	$I_F=0$, $V_O=V_{CC}=5.5\text{ V}$, $T_A=25^\circ\text{C}$
			.01	1		$I_F=0$, $V_O=V_{CC}=15\text{ V}$, $T_A=25^\circ\text{C}$
			—	50		$I_F=0$, $V_O=V_{CC}=15\text{ V}$
Capacitance	C_{CE}		3		pF	$V_{CE}=5\text{ V}$, $f=1\text{ MHz}$
Thermal Resistance	$R_{\theta JA}$		300		$^\circ\text{K/W}$	
Package						
Coupling Capacitance	C_C		0.6		pF	
Coupling Transfer Ratio	I_O/I_F	19	30		%	$I_F=16\text{ mA}$, $V_O=0.4\text{ V}$, $V_{CC}=4.5\text{ V}$, $T_A=25^\circ\text{C}$
		15	—			$I_F=16\text{ mA}$, $V_O=0.5\text{ V}$, $V_{CC}=4.5\text{ V}$
Collector Emitter Saturation Voltage	V_{OL}		0.1	0.4	V	$I_F=16\text{ mA}$; $I_O=2.4\text{ mA}$, $V_{CC}=4.5\text{ V}$, $T_A=25^\circ\text{C}$
Supply Current, Logic Low	I_{CCL}		80	200	μA	$I_F=16\text{ mA}$, V_O open, $V_{CC}=15\text{ V}$

Figure 1. Switching times (typ.)



Description	Symbol	Min.	Typ.	Max.	Unit
Propagation Delay Time (High–Low) $I_F=16\text{ mA}$, $V_{CC}=5\text{ V}$, $R_L=1.9\text{ k}\Omega$, $T_A=25^\circ\text{C}$	t_{PHL}		0.3	0.8	μs
Propagation Delay Time (Low–High) $I_F=16\text{ mA}$, $V_{CC}=5\text{ V}$, $R_L=1.9\text{ k}\Omega$, $T_A=25^\circ\text{C}$	t_{PLH}		0.3	0.8	μs

Figure 2. Common mode transient immunity



Description	Symbol	Min.	Typ.	Max.	Unit
Common Mode Transient Immunity (High) $I_F=0$, $V_{CM}=1500$ V _{P-P} , $R_L=1.9$ k Ω , $V_{CC}=5$ V, $T_A=25^\circ\text{C}$	$ CM_H $	15	30		kV/ μs
Common Mode Transient Immunity (Low) $I_F=16$ mA, $V_{CM}=1500$ V _{P-P} , $R_L=1.9$ k Ω , $V_{CC}=5$ V, $T_A=25^\circ\text{C}$	$ CM_L $	15	30		kV/ μs

Figure 3. LED forward current vs. forward voltage

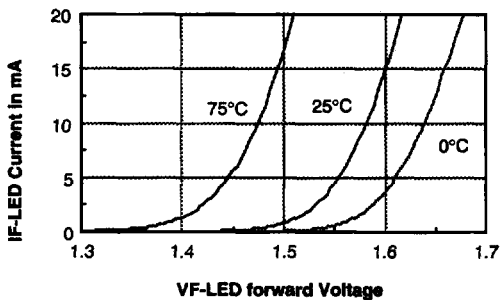


Figure 5. Permissible power dissipation vs. temp.

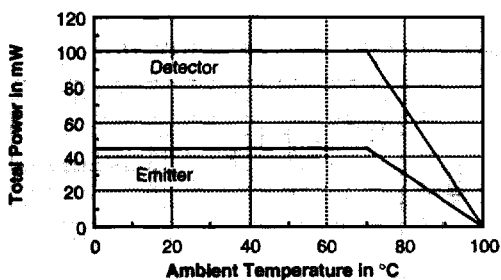


Figure 4. Permissible forward LED current vs. temperature

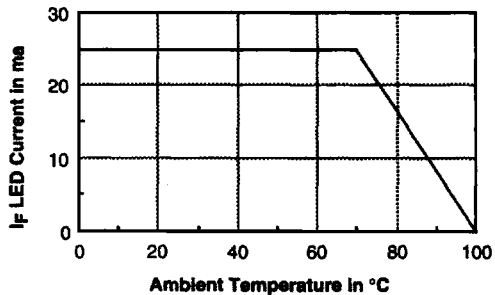


Figure 6. Output current vs. output voltage

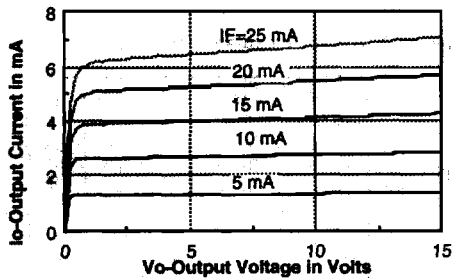


Figure 7. Output current (high) vs. temperature

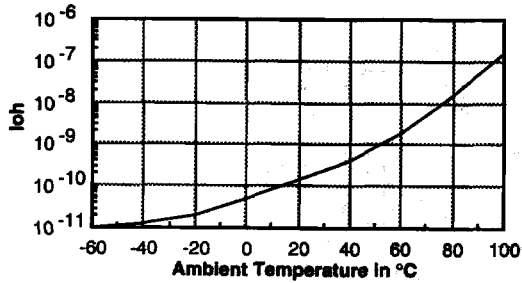


Figure 8. NCTR vs. IF

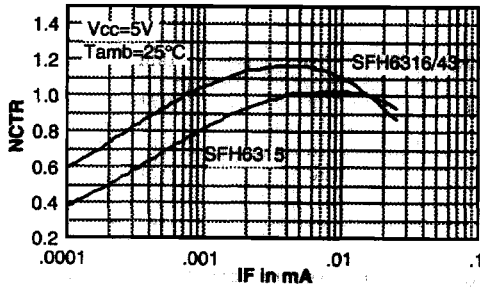


Figure 9. NCTR vs. temperature (SFH6316/43)

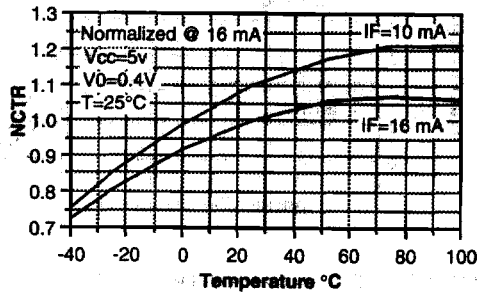


Figure 10. NCTR vs. temperature (SFH6315)

